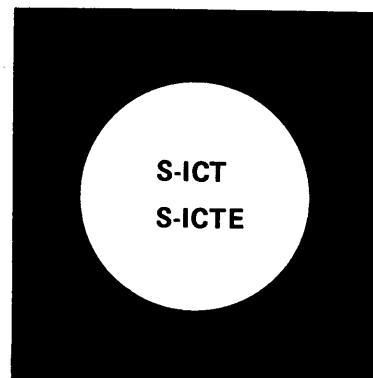


# Silicon Voltage Transient Suppressor Diodes

## I.C. TRANSIENT PROTECTORS 1.5 KW (D013) AND (EPOXY CASE)



### FEATURES

MOLDED OR METAL CASE

EPITAXIAL JUNCTION

LOW LEAKAGE

LOW  $V_Z$  /  $I_Z$  CHARACTERISTICS

VOLTAGE RANGE: 5.0 to 45 Volts

THE SICT SERIES HAS BEEN DESIGNED TO COVER THE MOST COMMON OPERATING VOLTAGE LEVELS OF A WIDE RANGE OF MICROPROCESSORS, MEMORIES, DIGITAL AND LINEAR ICs.

### MAXIMUM RATINGS

Peak Pulse Power Dissipation ( $T_A = 25^\circ C$ )	P <sub>p</sub>	1500 Watts
Peak Forward Surge Current ( $T_A = 25^\circ C$ , 8.3 msec)	I <sub>FM</sub>	200 Amps
Maximum Forward Voltage Drop (100A peak, 8.3 msec sine wave)	V <sub>F</sub>	2.0 Volts
D.C. Power Dissipation ( $T_A=25^\circ C$ ) S-ICT	P <sub>M</sub>	1 Watt
D.C. Power Dissipation ( $T_L=75^\circ C$ , Lead Length 3/8") S-ICTE	P <sub>M</sub>	5 Watts
Operating and Storage Temperature	T <sub>opr</sub> , T <sub>stg</sub>	-65°C to +175°C

### ELECTRICAL CHARACTERISTICS:

TYPE NUMBER		Reverse Stand-Off Voltage $V_R$ Volts	Maximum Reverse Leakage $I_R$ uA	Minimum Breakdown Voltage $B_V$ (min) Volts	Maximum Clamping Voltage $I_{pp} = 1 A$ $V_C$ Volts	Maximum Clamping Voltage $I_{pp} = 10 A$ $V_C$ Volts	Maximum Peak Pulse Current $I_{pp}$ A
SICT-5	SICTE-5	5.0	300	6.0	7.1	7.5	160
SICT-8	SICTE-8	8.0	25	9.4	11.3	11.5	100
SICT-10	SICTE-10	10.0	2	11.7	13.7	14.1	90
SICT-12	SICTE-12	12.0	2	14.1	16.1	16.5	70
SICT-15	SICTE-15	15.0	2	17.6	19.6	20.4	60
SICT-18	SICTE-18	18.0	2	21.2	24.2	25.2	50
SICT-22	SICTE-22	22.0	2	25.9	29.8	32.0	40
SICT-36	SICTE-36	36.0	2	42.4	50.6	54.3	23
SICT-45	SICTE-45	45.0	2	52.9	63.3	70.0	19

### ABBREVIATIONS AND SYMBOLS

$V_R$  Stand-Off Voltage. Maximum rated reverse voltage which can be applied to the SICT-Series with non-conducting condition. Cathode terminal positive.

$I_{pp}$  Peak Pulse Current

$P_p$  Peak Pulse Power

$I_R$  Reverse Leakage

$B_V$  (min) Minimum Breakdown Voltage

$V_C$  (max) Maximum Clamping Voltage. The maximum peak voltage appearing across the SICT-Series when subjected to the peak pulse current in a one millisecond time interval. The peak pulse voltages are the combination of voltage rise due to both the internal impedance and thermal rise.

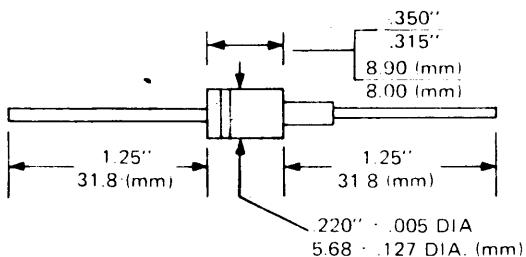
Semicon



AURIEMA GMBH

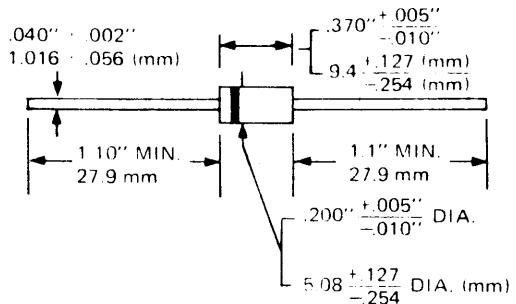
71 HEILBRONN, UHDESTRASS 33  
TELEFON 07131 / 5 30 66 · TELEX 07 28 639

CASE STYLE "A"



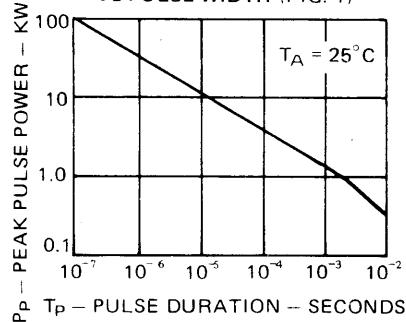
JEDEC DO-13 GLASS TO METAL CASE  
CATHODE IS COMMON TO CASE

CASE STYLE "B"

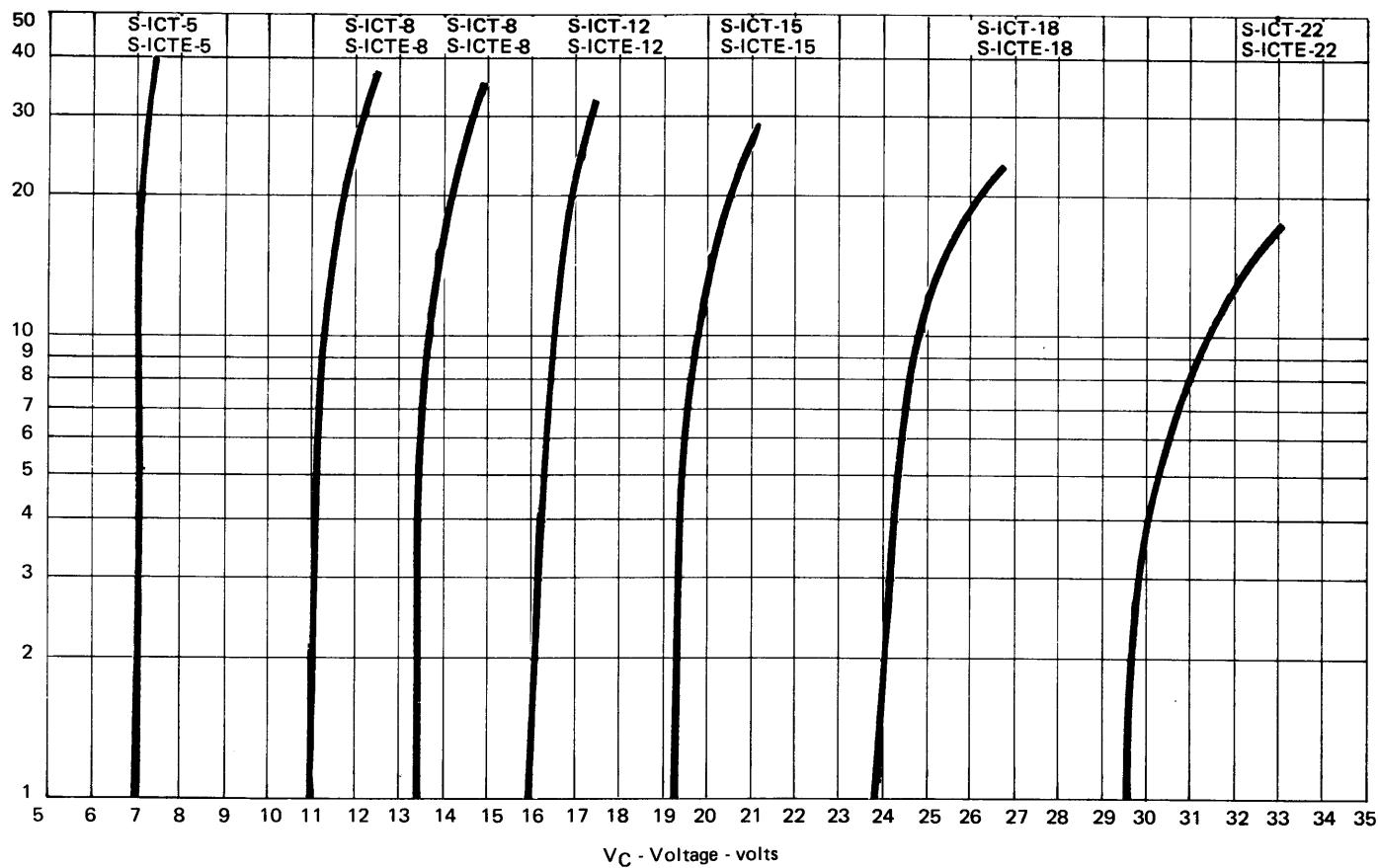
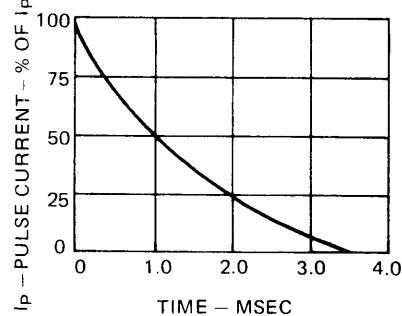


EPOXY MOLDED CASE:  
POLARITY INDICATED BY BAND OR SYMBOL

MAXIMUM ALLOWABLE PEAK PULSE POWER  
VS PULSE WIDTH (FIG. 1)



PULSE CURRENT VS TIME (FIG. 2)



Typical Characteristic Clamping Voltage (Vc) vs Peak Pulse Current (Ipp)



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